

**AMENDMENT TO THE SPECIFICATION**

Please amend the paragraph beginning on page 12, line 23 and ending on page 13, line 10 as follows:

--Subsequently, on the strain suppression layer **13**, formed sequentially are n-type contact layer **14** made of n-type GaN, an n-type cladding layer **15** made of n-type  $\text{Al}_{0.07}\text{Ga}_{0.93}\text{N}$ , an n-type optical guide layer **16** made of n-type GaN, a multiple quantum well (MQW) active layer **17** made of a GaInN/GaN multilayer structure, a p-type cap layer **18** made of p-type  $\text{Al}_{0.14}\text{Ga}_{0.86}\text{N}$ , a p-type optical guide layer **19** made of p-type GaN, a p-type superlattice cladding layer **20** made of a p-type  $\text{Al}_{0.14}\text{Ga}_{0.86}\text{N}/\text{GaN}$  ~~multiplayer~~ multilayer structure, a p-type second contact layer **21** made of p-type GaN, and a p-type first contact layer **22** made of p-type GaN having an impurity concentration higher than that of the p-type second contact layer **21** to reduce the resistance.--